



# STI260N6F6 STP260N6F6

N-channel 60 V, 0.0024  $\Omega$ , 120 A STripFET™ VI DeepGATE™  
Power MOSFET in TO-220 and I<sup>2</sup>PAK packages

## Features

Order codes	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STI260N6F6 STP260N6F6	60 V	< 0.003 $\Omega$	120 A

- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

## Application

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFETs exhibits the lowest R<sub>DS(on)</sub> in all packages.

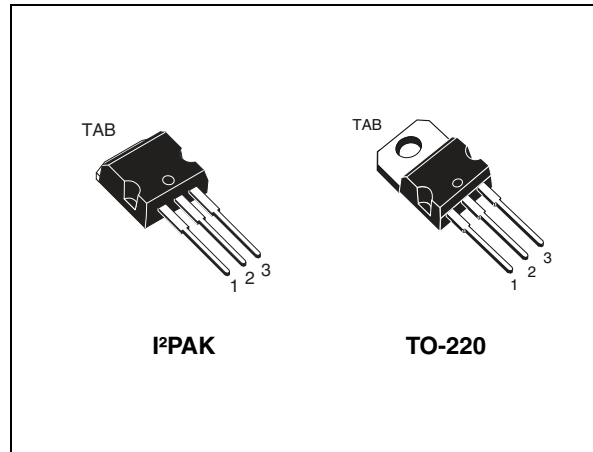


Figure 1. Internal schematic diagram

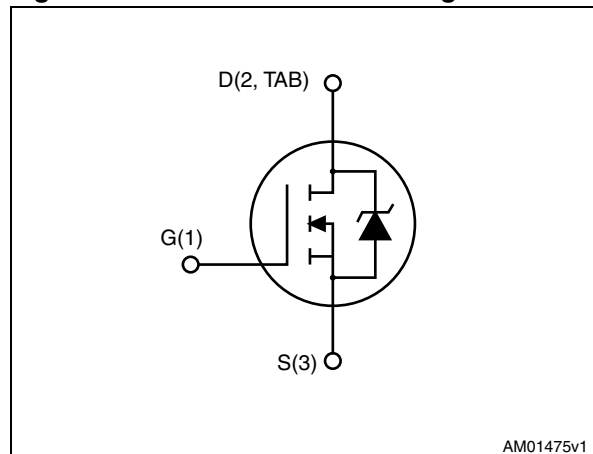


Table 1. Device summary

Order codes	Marking	Package	Packaging
STI260N6F6	260N6F6	I <sup>2</sup> PAK	Tube
STP260N6F6		TO-220	

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	60	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(1)}$	Drain current (pulsed)	480	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$T_{stg}$	Storage temperature	- 55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature		

1. Current limited by package.

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS} = 0$ )	$I_D = 250\ \mu A$	60			V
$I_{DSS}$	Zero gate voltage Drain current ( $V_{GS} = 0$ )	$V_{DS} = 60\ V$ $V_{DS} = 60\ V, T_C = 125\text{ °C}$			1 100	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\ V$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ V, I_D = 60\ A$		2.4	3	m $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance			11400		pF
$C_{oss}$	Output capacitance	$V_{DS} = 25\ V, f = 1\ MHz,$ $V_{GS} = 0$	-	850	-	pF
$C_{rss}$	Reverse transfer capacitance			368		pF
$Q_g$	Total gate charge	$V_{DD} = 30\ V, I_D = 120\ A,$ $V_{GS} = 10\ V$ <i>(see Figure 14)</i>		183		nC
$Q_{gs}$	Gate-source charge		-	53	-	nC
$Q_{gd}$	Gate-drain charge			41		nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\ V, I_D = 60\ A$ $R_G = 4.7\ \Omega, V_{GS} = 10\ V$ <i>(see Figure 13)</i>	-	31.4	-	ns
$t_r$	Rise time			165		
$t_{d(off)}$	Turn-off-delay time	$V_{DD} = 30\ V, I_D = 60\ A$ $R_G = 4.7\ \Omega, V_{GS} = 10\ V$ <i>(see Figure 13)</i>	-	144.4	-	ns
$t_f$	Fall time			62.6		

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120 \text{ A}, V_{GS} = 0$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 120 \text{ A}, V_{DD} = 48 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$ , $T_j = 150 \text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	55.6		ns
$Q_{rr}$	Reverse recovery charge			116		nC
$I_{RRM}$	Reverse recovery current			3.8		A

1. Current limited by package.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

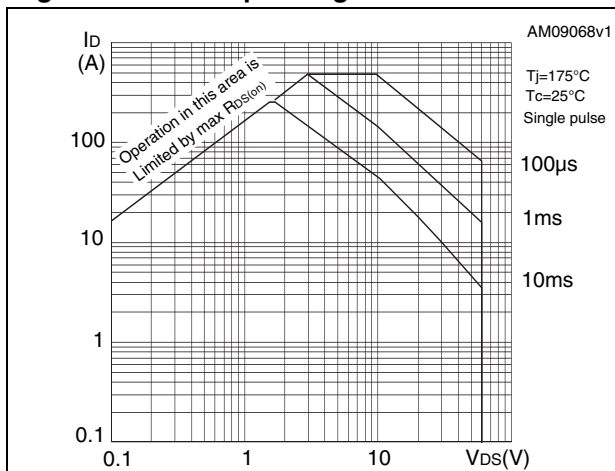


Figure 3. Thermal impedance

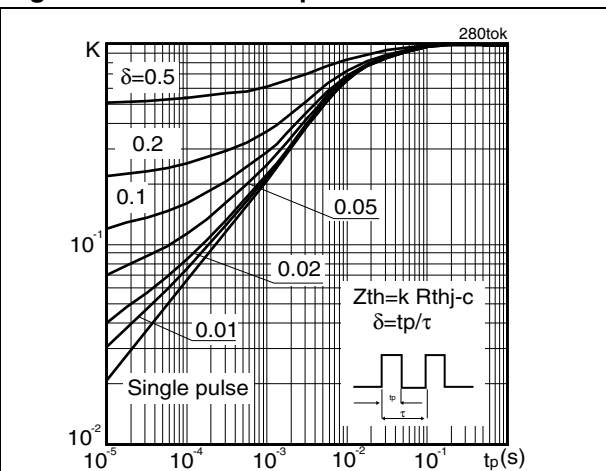


Figure 4. Output characteristics

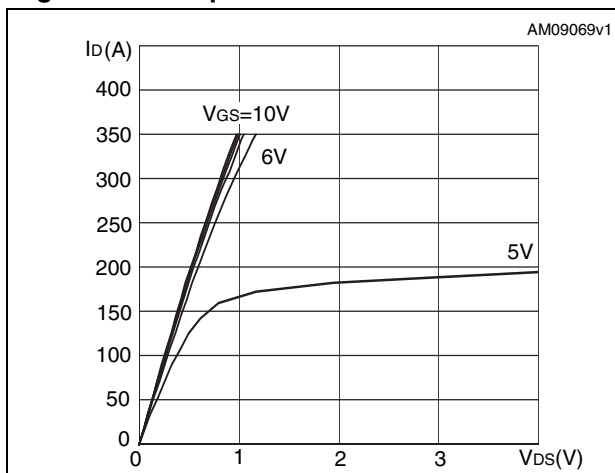


Figure 5. Transfer characteristics

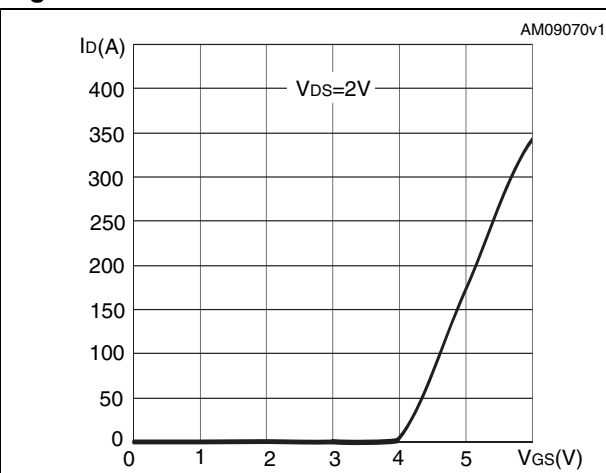


Figure 6. Normalized  $B_{V_{DSS}}$  vs. temperature

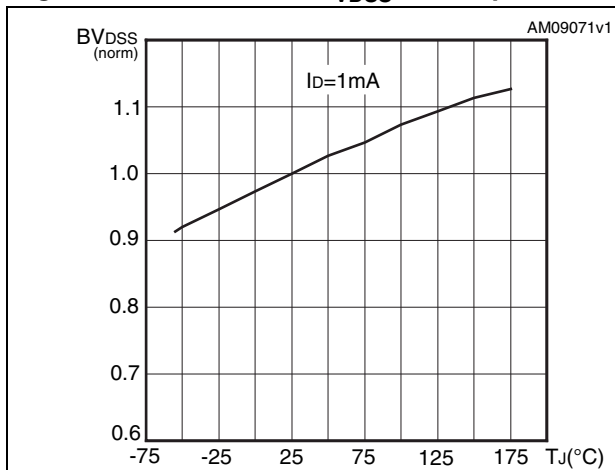
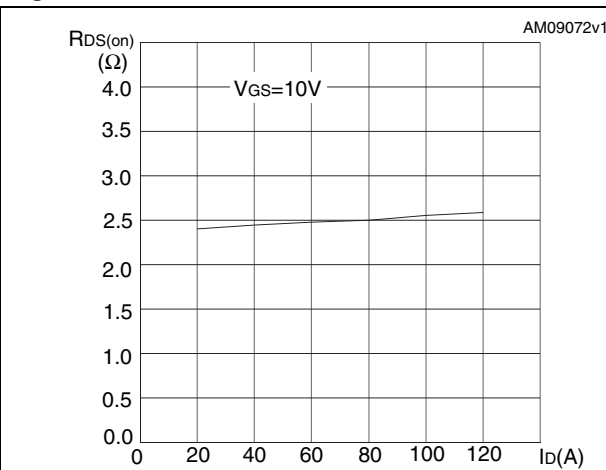
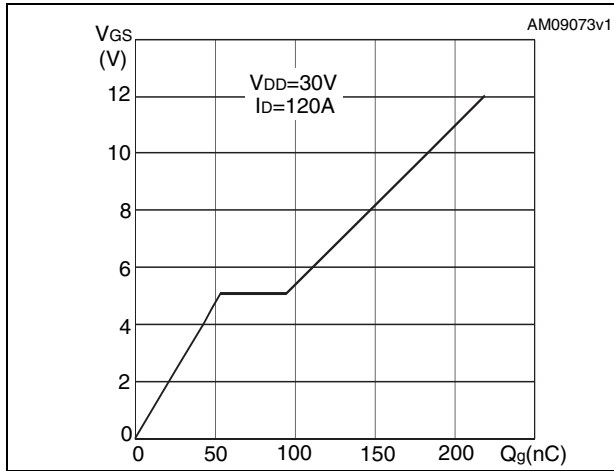


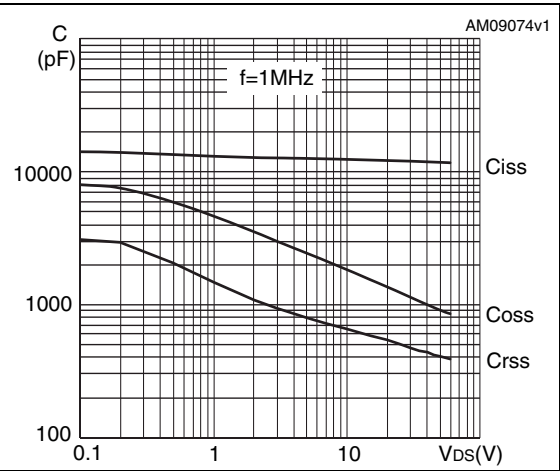
Figure 7. Static drain-source on resistance



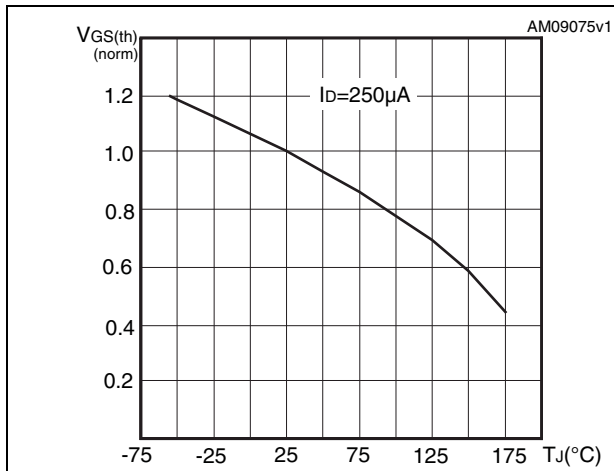
**Figure 8. Gate charge vs. gate-source voltage**



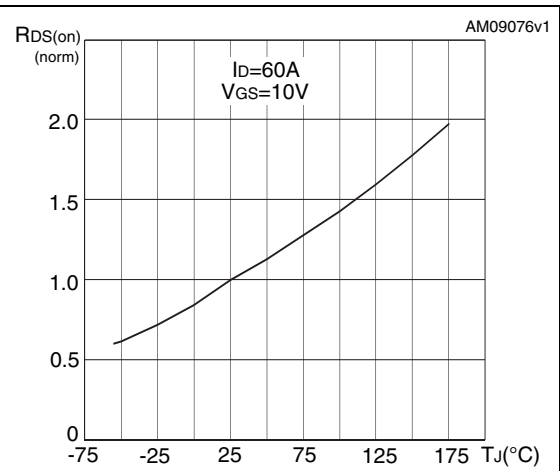
**Figure 9. Capacitance variations**



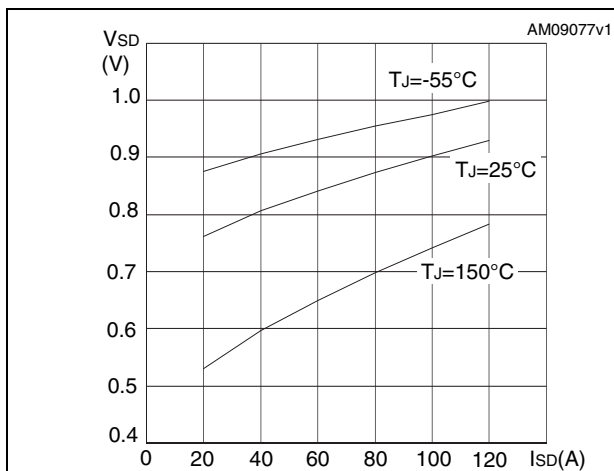
**Figure 10. Normalized gate threshold voltage vs. temperature**



**Figure 11. Normalized on resistance vs. temperature**

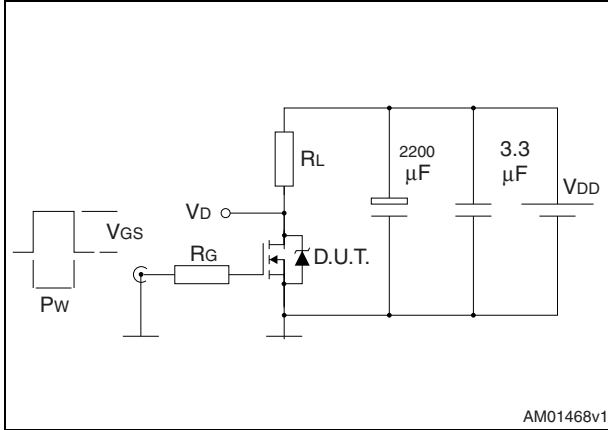


**Figure 12. Source-drain diode forward characteristics**



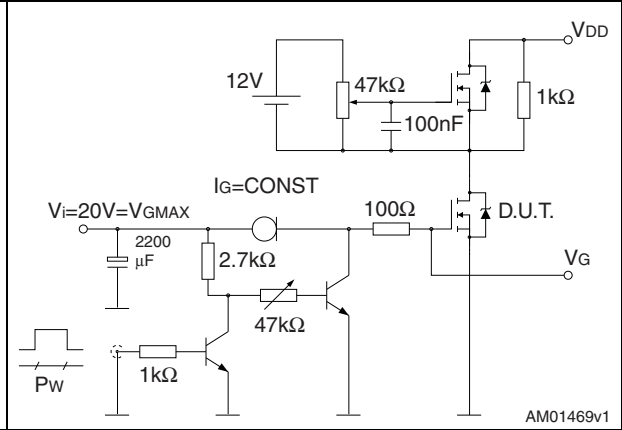
### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



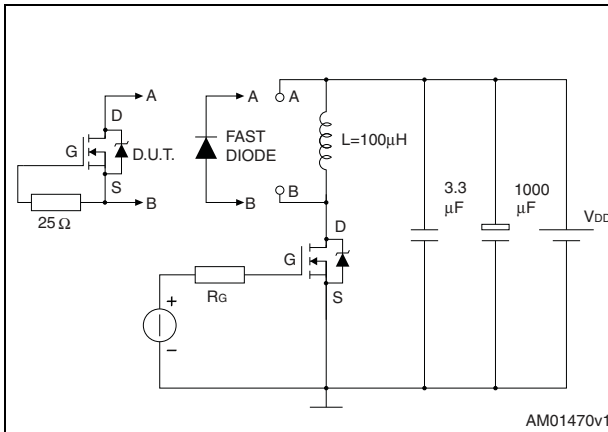
AM01468v1

**Figure 14. Gate charge test circuit**



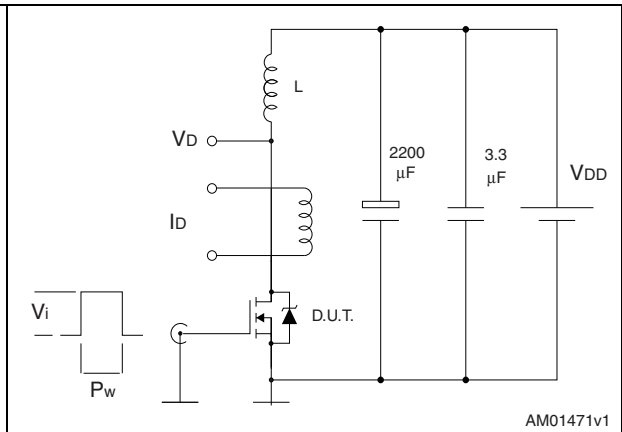
AM01469v1

**Figure 15. Test circuit for inductive load switching and diode recovery times**



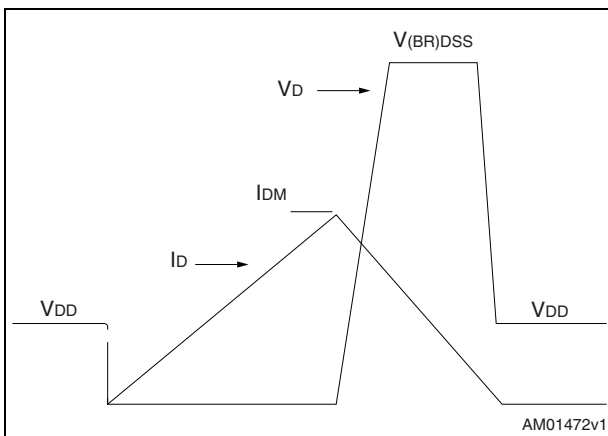
AM01470v1

**Figure 16. Unclamped inductive load test circuit**



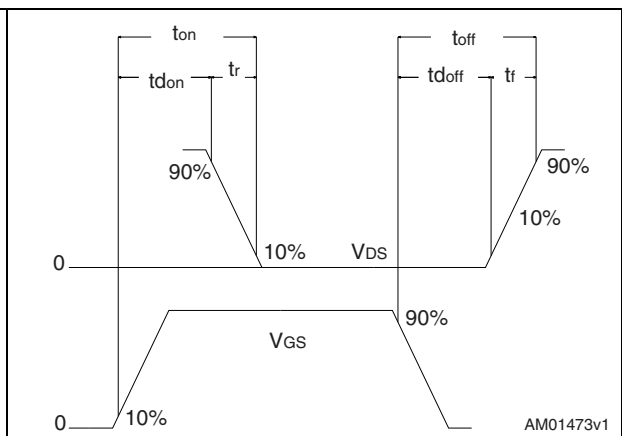
AM01471v1

**Figure 17. Unclamped inductive waveform**



AM01472v1

**Figure 18. Switching time waveform**



AM01473v1



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 8. I<sup>2</sup>PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 19. I<sup>2</sup>PAK (TO-262) drawing

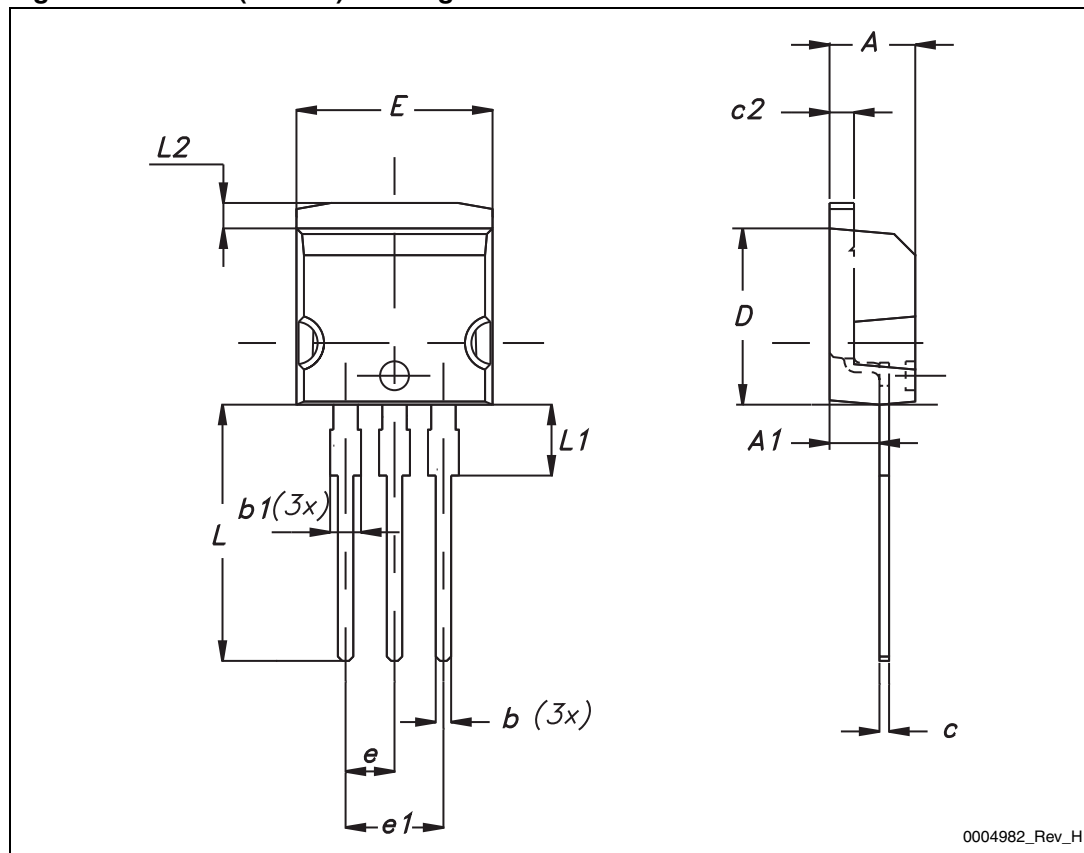
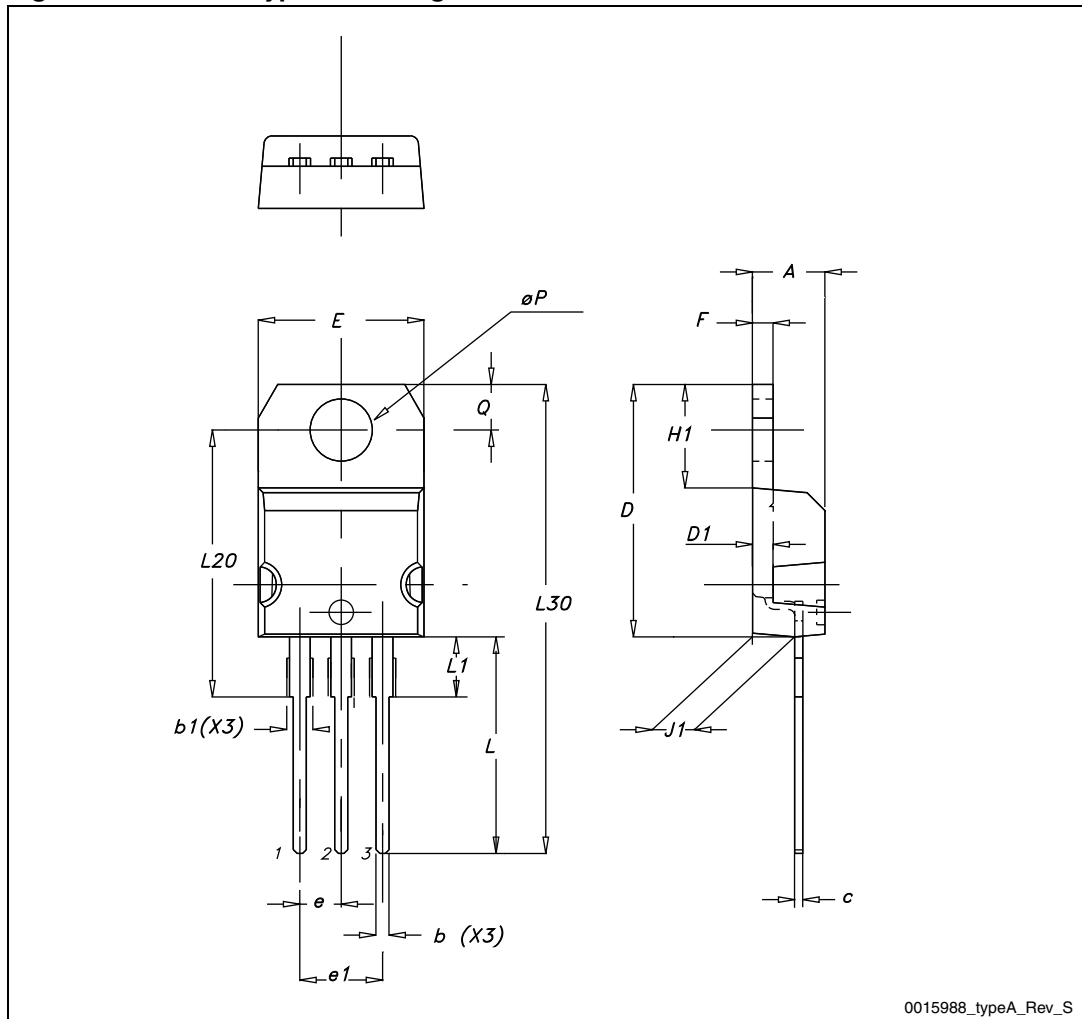


Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 20. TO-220 type A drawing



## 5 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
07-May-2010	1	First release.
18-Apr-2011	2	Document status promoted from preliminary data to datasheet.
27-Apr-2011	3	<i>Device summary</i> has been updated.
05-Oct-2011	4	<i>Table 2: Absolute maximum ratings</i> has been updated. Minor text changes.
13-Jan-2012	5	Updated <i>Table 2: Absolute maximum ratings</i> .

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